

PMEG3020EP 2 A low V_F MEGA Schottky barrier rectifier Rev. 01 — 15 September 2009

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: $I_{F(AV)} \le 2 A$
- Reverse voltage: $V_R \le 30 \text{ V}$
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1. Quick reference data

 $T_i = 25 \circ C$ unless otherwise specified.

,	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)} average forward current		square wave; $\delta = 0.5;$ f = 20 kHz				
		$T_{amb} \le 110 \ ^{\circ}C$	<u>[1]</u> _	-	2	А
		$T_{sp} \le 140 \ ^{\circ}C$	-	-	2	А
V _R	reverse voltage		-	-	30	V
V _F	forward voltage	I _F = 2 A	-	310	360	mV
I _R	reverse current	V _R = 30 V	-	1	3	mA

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	
2	anode	1 2	1 🕂 2
			sym001

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Orde	ering inforr	nation	
Type number	Package		
	Name	Description	Version
PMEG3020EP	-	plastic surface-mounted package; 2 leads	SOD128

4. Marking

Table 4. Marking code	s
Type number	Marking code
PMEG3020EP	A3

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0 7 (/		
Symbol	Parameter	Conditions	Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C	-	30	V
I _{F(AV)}	average forward current	square wave; δ = 0.5; f = 20 kHz			
		$T_{amb} \le 110 \ ^{\circ}C$	<u>[1]</u> -	2	А
		$T_{sp} \le 140 \ ^{\circ}C$	-	2	А
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[2] -	50	A
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[3][4] _	625	mW
			[3][5] _	1050	mW
			[3][1]	2100	mW

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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[2] $T_j = 25 \ ^{\circ}C$ prior to surge.

[3] Reflow soldering is the only recommended soldering method.

- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1][2]			
	junction to ambient		[3] _	-	200	K/W
			[4] _	-	120	K/W
			[5] _	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

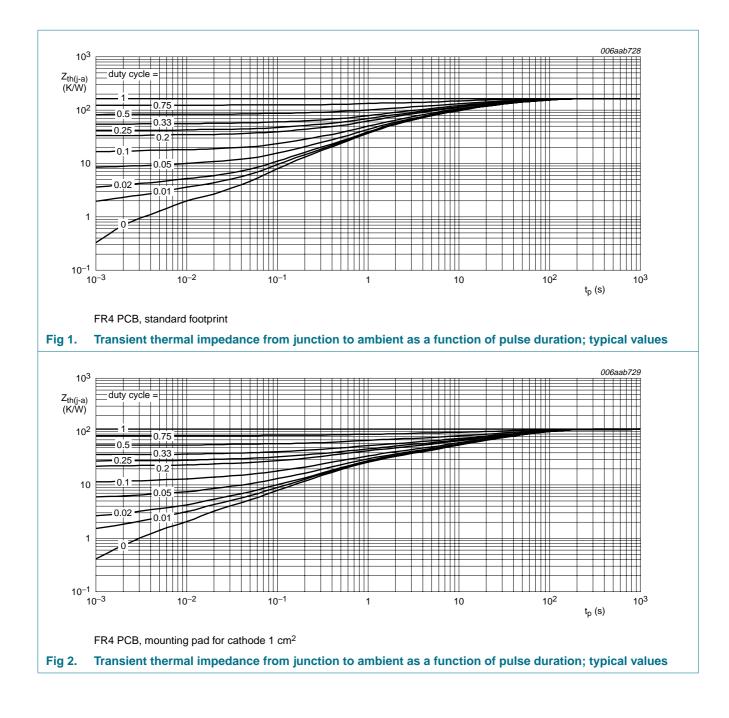
[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[5] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

[6] Soldering point of cathode tab.

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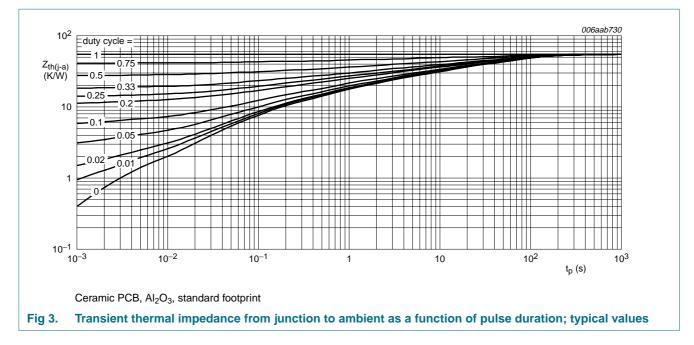
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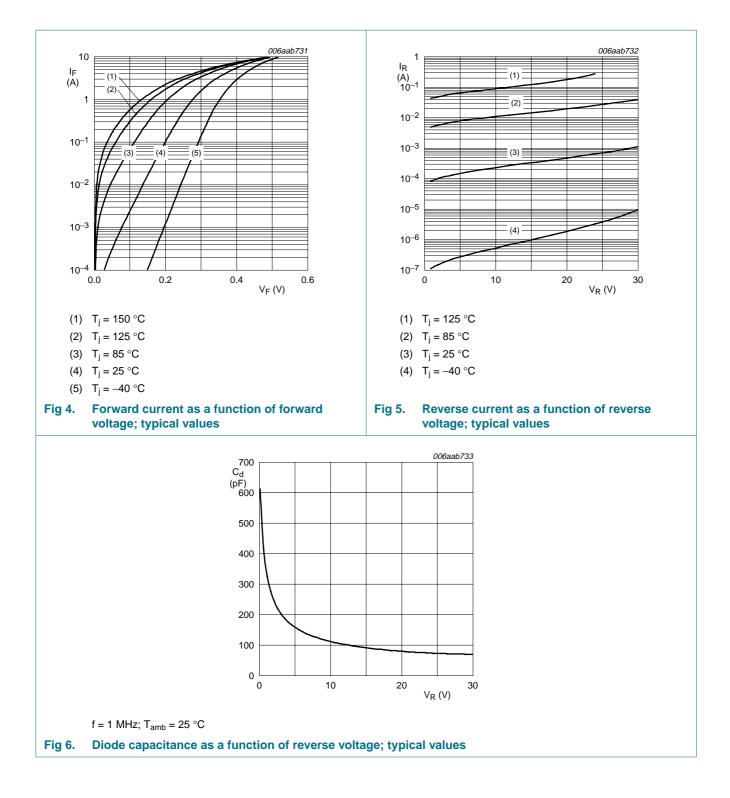


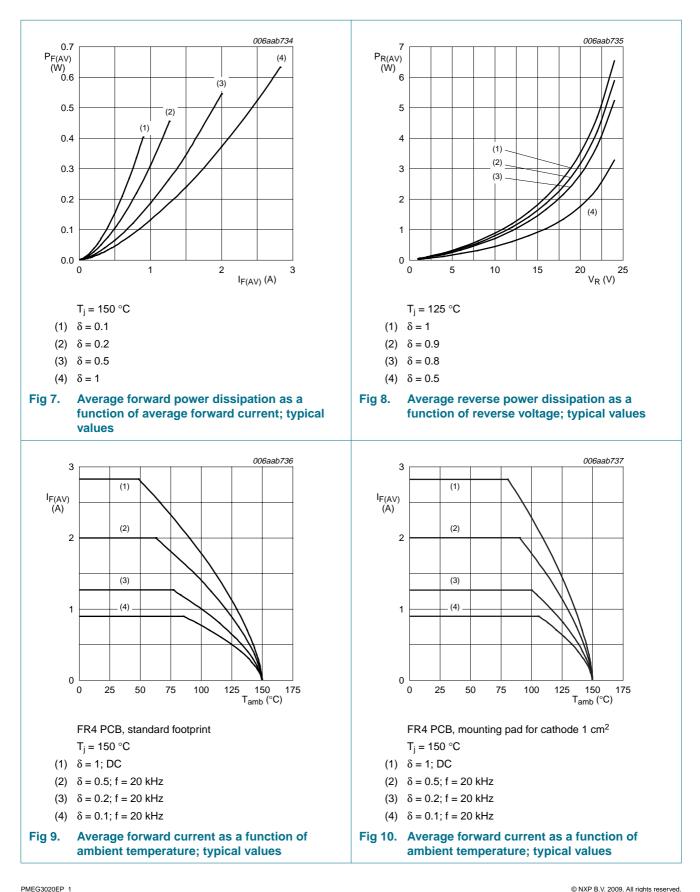
7. Characteristics

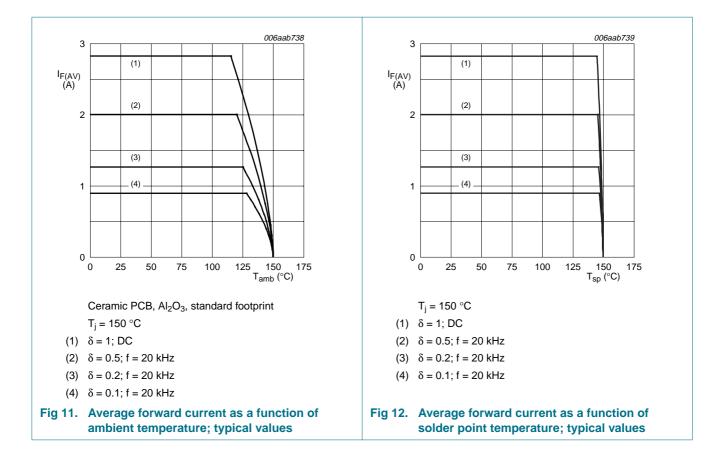
 Table 7.
 Characteristics

Ti	= 25 °C	unless	otherwise	specified.
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I _F = 0.5 A	-	250	280	mV
	I _F = 1 A	-	275	310	mV	
	I _F = 2 A	-	310	360	mV	
I _R	reverse current	V _R = 5 V	-	130	-	μA
	V _R = 30 V	-	1	3	mA	
C _d	diode capacitance	f = 1 MHz				
	$V_R = 1 V$	-	325	-	pF	
		V _R = 10 V	-	110	-	pF

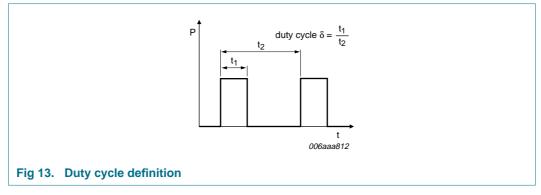






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8. Test information

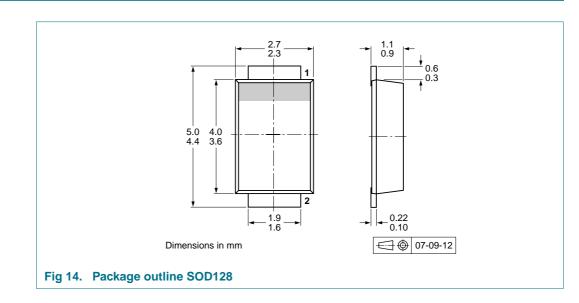


The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

 $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.



9. Package outline

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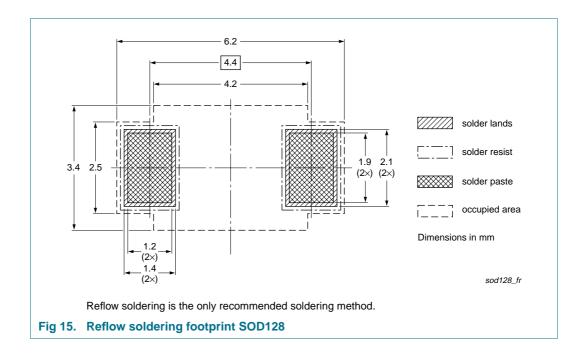
2 A low V_F MEGA Schottky barrier rectifier

10. Packing information

	king methods xx are the las	s t three digits of the 12NC ordering code. ^[1]	
Type number	Package	Description	Packing quantity
			3000
PMEG3020EP	SOD128	4 mm pitch, 12 mm tape and reel	-115
[d] Eastwelle as inf		he evolution of peaking methods, and Caption 14	

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

11. Soldering



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12. Revision history

Table 9. Re	evision histo	ory			
Document ID)	Release date	Data sheet status	Change notice	Supersedes
PMEG3020EF	P_1	20090915	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

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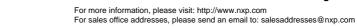
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